
2SC4367

Silicon NPN Epitaxial

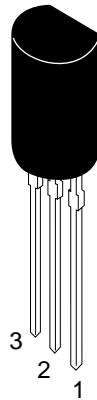
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Application

High Frequency amplifier

Outline

TO-92MOD



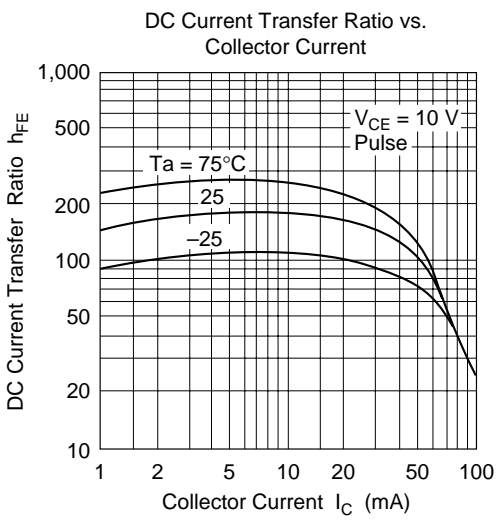
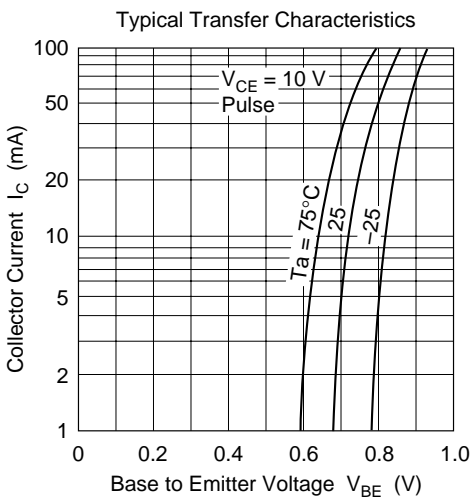
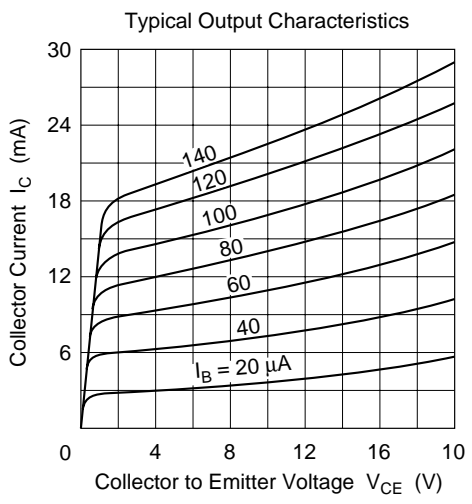
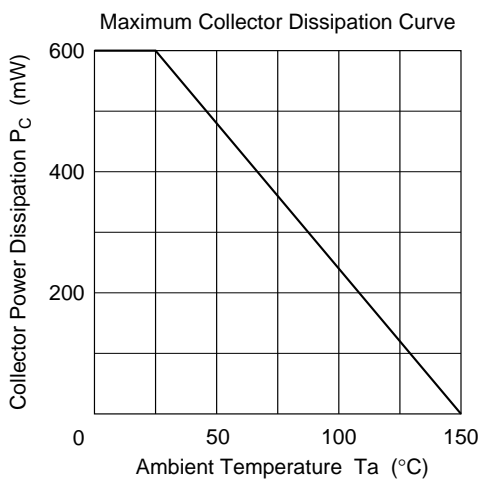
- 1. Emitter
- 2. Collector
- 3. Base

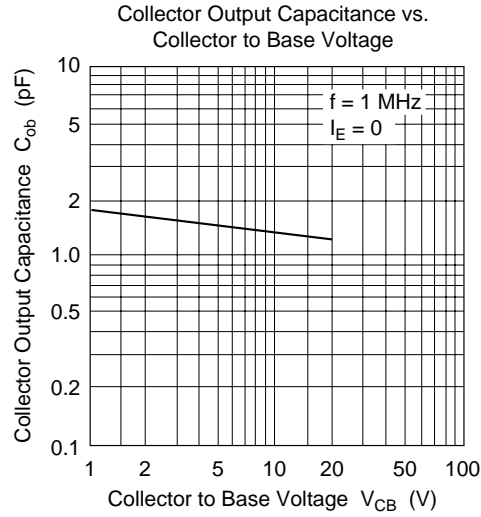
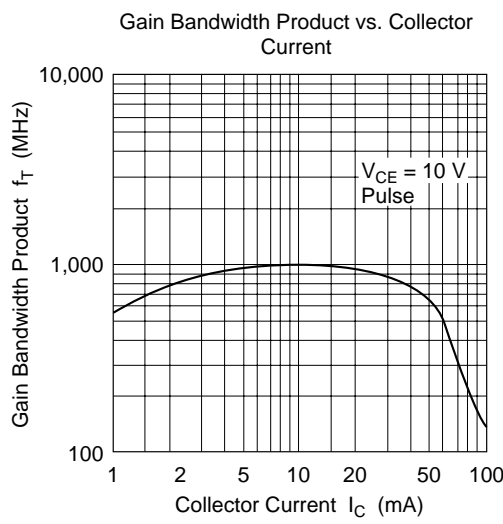
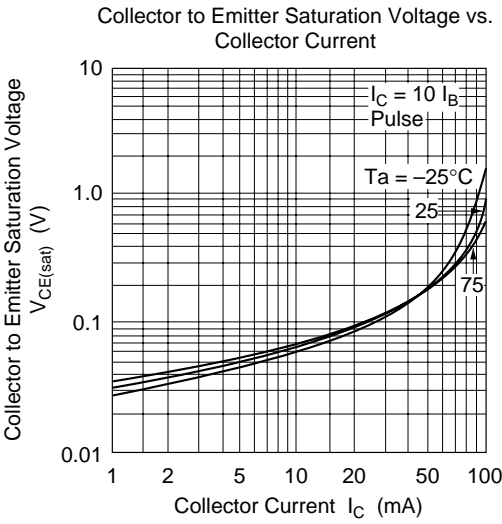
Absolute Maximum Ratings (Ta = 25°C)

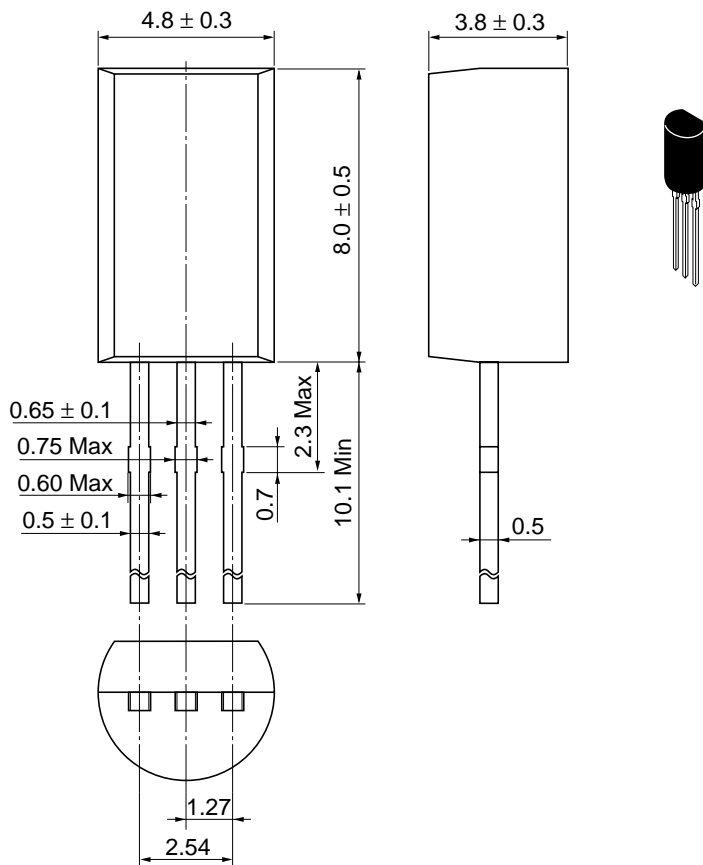
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	30	V
Collector to emitter voltage	V_{CEO}	20	V
Emitter to base voltage	V_{EBO}	3	V
Collector current	I_C	100	mA
Collector peak current	$i_{C\text{ (peak)}}$	200	mA
Collector power dissipation	P_C	600	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	—	—	V	$I_C = 10\text{ }\mu\text{A}$, $I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	20	—	—	V	$I_C = 3\text{ mA}$, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	3	—	—	V	$I_E = 10\text{ }\mu\text{A}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	1.0	μA	$V_{CB} = 10\text{ V}$, $I_E = 0$
DC current transfer ratio	h_{FE}	40	—	—		$V_{CE} = 10\text{ V}$, $I_C = 10\text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1.0	V	$I_C = 20\text{ mA}$, $I_B = 4\text{ mA}$
Gain bandwidth product	f_T	600	1000	—	MHz	$V_{CE} = 10\text{ V}$, $I_C = 10\text{ mA}$
Collector output capacitance	C_{ob}	—	1.3	—	pF	$V_{CB} = 10\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$







Hitachi Code	TO-92 Mod
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.35 g

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